Structure

Silicon N-channel MOSFET

Features

- 1) Low On-resistance.
- 2) 4V drive.

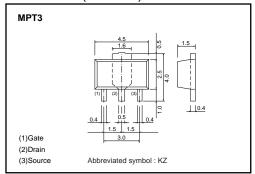
Applications

Switching

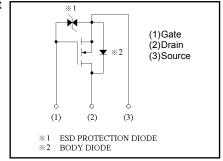
Packaging specifications

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	Package	Taping		
Type	Code	T100		
	Basic ordering unit (pieces)	1000		
RHP030N03		0		

●Dimensions (Unit : mm)



●Inner circuit



●Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		V_{DSS}	30	V
Gate-source voltage		V _{GSS}	±20	V
Danier account	Continuous	ID	3	Α
Drain current	Pulsed I _{DP}		10	Α
Reverse drain current	Continuous	Idr	3	Α
Neverse drain current	Pulsed	I _{DRP} *1	10	Α
Total power dissipation		Ь	500	mW
		P _D	2 *2	W
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	-55 to +150	°C

●Thermal resistance

- 111011110111101				
Parameter	Symbol	Limits	Unit	
Channel to ambient	Dth(oh o)	250	°C/W	
Charmer to ambient	Rth(ch-a)	62.5 *	°C/W	

^{*} When mounted on a 40×40×0.7mm ceramic board

^{*1} Pw≤10µs, Duty cycle≤1% *2 When mounted on a 40×40×0.7mm ceramic board

Data Sheet

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	I _{GSS}	_	_	±10	μА	V _{GS} =±20V, V _{DS} =0V
Drain-source breakdown voltage	V _(BR) DSS	30	_	_	V	I _D = 1mA, V _{GS} =0V
Zero gate voltage drain current	I _{DSS}	_	-	1	μА	V _{DS} = 30V, V _{GS} =0V
Gate threshold voltage	V _{GS (th)}	1.0	-	2.5	V	V _{DS} = 10V, I _D = 1mA
Static drain-source on-state resistance	R _{DS (on)} *	_	90	120	mΩ	ID= 3A, VGS= 10V
		_	160	210	mΩ	I _D = 3A, V _{GS} = 4V
Forward transfer admittance	Y _{fs} *	2.0	-	_	S	V _{DS} = 10V, I _D = 3A
Input capacitance	Ciss	_	160	_	pF	V _{DS} = 10V
Output capacitance	Coss	-	90	_	pF	V _{GS} =0V
Reverse transfer capacitance	Crss	_	27	_	pF	f=1MHz
Turn-on delay time	t d (on) *	_	7	_	ns	V _{DD} ≒ 15V
Rise time	tr *	_	11	_	ns	I _D = 1.5A V _G s= 10V
Turn-off delay time	t _{d (off)} *	_	15	_	ns	VGS= 10V RL=10Ω
Fall time	t _f *	_	4.5	_	ns	R _G =10Ω
Total gate charge	Qg *	_	6.5	_	nC	V _{DD} ≒15V
Gate-source charge	Q _{gs} *	-	1.0	-	nC	V _{GS} = 10V
Gate-drain charge	Q _{gd} *	_	1.5	_	nC	ID= 3A

^{*}Pulsed

•Electrical characteristics curves

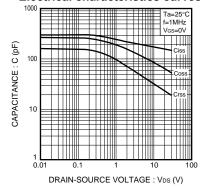


Fig.1 Typical Capacitance vs. Drain-Source Voltage

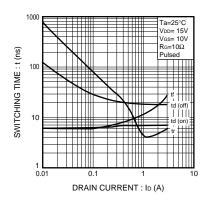


Fig.2 Switching Characteristics

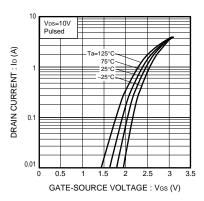


Fig.3 Typical Transfer Characteristics

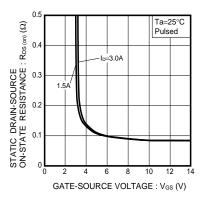


Fig.4 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

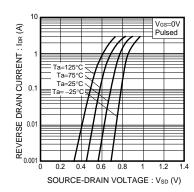


Fig.5 Reverse Drain Current vs. Source-Drain Voltage (I)

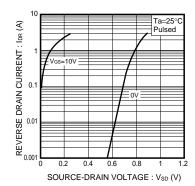


Fig.6 Reverse Drain Current vs. Source-Drain Voltage (II)

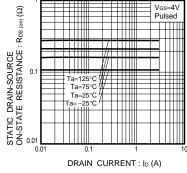


Fig.8 Static Drain-Source On-State Resistance vs. Drain Current (II)

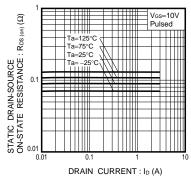


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current (I)

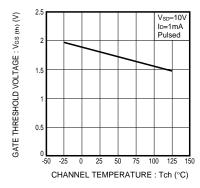


Fig.9 Gate Threshold Voltage vs. Channel Temperature

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